

TECHNIQUES FOR COUPLING PLANAR QUBITS TO NON-PLANAR RESONATORS AND RELATED SYSTEMS AND METHODS

CROSS REFERENCE TO RELATED APPLICATIONS

[0001] This application claims the benefit under 35 U.S.C. §119(e) of U.S. Provisional Patent Application No. 62/126,183, filed February 27, 2015, titled “Coupling Planar Qubits to Non-Planar Resonators,” which is hereby incorporated by reference in its entirety.

STATEMENT REGARDING FEDERALLY-SPONSORED RESEARCH AND DEVELOPMENT

[0002] This invention was made with U.S. Government support under Grant No. W911NF-14-1-0011 awarded by the U.S. Army Research Office. The U.S. Government may have certain rights in this invention.

FIELD

[0003] The present application relates generally to quantum information processing. More specifically, the present application relates to coupling a planar quantum system to a non-planar resonator or resonant structure.

BACKGROUND

[0004] Quantum information processing uses quantum mechanical phenomena, such as energy quantization, superposition, and entanglement, to encode and process information in a way not utilized by conventional information processing. For example, certain computational problems may be solved more efficiently using quantum computation rather than conventional classical computation. However, to become a viable computational option, it may be necessary to precisely control a large number of quantum bits, known as “qubits,” and to control interactions between these qubits. In particular, qubits may ideally have long coherence times, be able to be individually manipulated, be able to interact with one or more other qubits to implement multi-qubit

gates, be able to be initialized and measured efficiently, and be scalable so that a quantum computer can include large numbers of qubits.

[0005] A qubit may be formed from any physical quantum mechanical system with at least two orthogonal states. The two states of the system used to encode information are referred to as the “computational basis.” For example, photon polarization, electron spin, and nuclear spin are all two-level systems that may encode information and may therefore each be used as a qubit for quantum information processing. Different physical implementations of qubits have different advantages and disadvantages. For example, photon polarization benefits from long coherence times and simple single qubit manipulation, but suffers from the inability to create simple multi-qubit gates.

[0006] Different types of superconducting qubits using Josephson junctions have been proposed, including “phase qubits,” where the computational basis is the quantized energy states of Cooper pairs in a Josephson Junction; “flux qubits,” where the computational basis is the direction of circulating current flow in a superconducting loop; and “charge qubits,” where the computational basis is the presence or absence of a Cooper pair on a superconducting island. Superconducting qubits are an advantageous choice of qubit because the coupling between two qubits is strong, making two-qubit gates relatively simple to implement, and superconducting qubits are scalable because they are mesoscopic components that may be formed using conventional electronic circuitry techniques.

SUMMARY

[0007] Some aspects are directed to quantum mechanical system, comprising a resonator having a plurality of superconducting surfaces and configured to support at least one electromagnetic oscillation mode within a three-dimensional region, wherein the plurality of superconducting surfaces include a first superconducting surface that defines a first plane, and a physical qubit comprising at least one planar component that is planar within the first plane and borders the three-dimensional region.

[0008] According to some embodiments, the at least one planar component includes at least one Josephson element.

[0009] According to some embodiments, the at least one planar component includes a superconducting patch antenna.

[0010] According to some embodiments, the superconducting patch antenna comprises a patch with a circular shape.

[0011] According to some embodiments, the superconducting patch antenna comprises a patch with a rectangular shape.

[0012] According to some embodiments, a superconducting patch of the superconducting patch antenna is connected to the first superconducting surface via at least one Josephson element.

[0013] According to some embodiments, the resonator is a three dimensional cavity resonator.

[0014] According to some embodiments, the resonator is a whispering gallery mode resonator.

[0015] According to some embodiments, the whispering gallery mode resonator includes the first superconducting surface and a second superconducting surface parallel to the first superconducting surface, and wherein the first superconducting surface is separated from the second superconducting surface by a first distance.

[0016] According to some embodiments, the whispering gallery mode resonator supports at least two electromagnetic oscillation modes.

[0017] According to some embodiments, the at least two electromagnetic oscillation modes are differential modes.

[0018] According to some embodiments, a first electromagnetic oscillation mode of the at least two electromagnetic oscillation modes is a parallel mode.

[0019] According to some embodiments, a second electromagnetic oscillation mode of the at least two electromagnetic oscillation modes is a perpendicular mode.

[0020] According to some embodiments, the first superconducting surface is a first ring-like structure and the second superconducting surface is a second ring-like structure.

[0021] According to some embodiments, the first ring-like structure is circularly asymmetric such that a first width of the first ring-like structure in the first plane at a first location is less than a second width of the first ring-like structure in the first plane at a second location, different from the first location.

[0022] According to some embodiments, the quantum mechanical system comprises a plurality of resonators.

[0023] According to some embodiments, a first resonator of the a plurality of resonators is a readout cavity.

[0024] According to some embodiments, a second resonator of the a plurality of resonators is a storage cavity.

BRIEF DESCRIPTION OF DRAWINGS

[0025] Various aspects and embodiments will be described with reference to the following figures. It should be appreciated that the figures are not necessarily drawn to scale. In the drawings, each identical or nearly identical component that is illustrated in various figures is represented by a like numeral. For purposes of clarity, not every component may be labeled in every drawing.

[0026] FIG. 1 illustrates a conventional quantum device;

[0027] FIG. 2 illustrates a quantum device in which a planar qubit is coupled to a non-planar resonator, according to some embodiments;

[0028] FIG. 3A is a top view of a patch antenna, according to some embodiments;

[0029] FIG. 3B is a cross-sectional view of a patch antenna, according to some embodiments;

[0030] FIG. 4A is a cross-sectional view of a quantum device comprising a three-dimensional cavity resonator, according to some embodiments;

[0031] FIG. 4B is a perspective view of a qubit and one superconducting portion of a three-dimensional cavity resonator, according to some embodiments;

[0032] FIG. 5 is a cross-sectional view of a quantum device comprising two three-dimensional cavity resonators, according to some embodiments;

[0033] FIG. 6A is a perspective view of a parallel plate transmission line;

[0034] FIG. 6B is a perspective view of a whispering gallery mode resonator, according to some embodiments;

[0035] FIG. 6C is a cross-sectional view of a whispering gallery mode resonator, according to some embodiments;

[0036] FIG. 7A is a top view of a qubit in a first location within a whispering gallery mode resonator, according to some embodiments;

[0037] FIG. 7B is a top view of a qubit in a second location within a whispering gallery mode resonator, according to some embodiments;

[0038] FIG. 8 is a detailed top view of a qubit in a whispering gallery mode resonator, according to some embodiments;

[0039] FIGs. 9A-9J illustrate cross-sectional views of acts of a method of forming a superconducting device, according to some embodiments;

[0040] FIG. 10 illustrates a trough resulting from an anisotropic wet etch, according to some embodiments;

[0041] FIG. 11 is a flow chart of a method of forming a superconducting device, according to some embodiments; and

[0042] FIG. 12 is a flow chart of a method of forming a trough within a superconducting device, according to some embodiments.

DETAILED DESCRIPTION

[0043] As discussed above, superconducting qubits are an advantageous choice of qubit in building a quantum computation device. In particular, superconducting qubits can be fabricated using standard two-dimensional fabrication techniques such as lithography, making them scalable. On the other hand, superconducting qubits suffer from having shorter coherence times than other devices for storing quantum information. As such, superconducting qubits are often coupled to interact with electromagnetic radiation, such as standing waves within a resonant cavity or other oscillator, to form a three-dimensional circuit. Since a resonator typically offers much greater coherence times than a superconducting qubit, a combination of the two devices into a “logical” qubit may offer a longer coherence time.

[0044] FIG. 1 illustrates an example of a conventional quantum device 100 in which a superconducting qubit 110 is placed within a cavity resonator defined by reflectors 131 and 132. The qubit 110 includes a Josephson junction 116 (indicated as an “X” in the drawing) connected to two superconducting blocks 112 and 114 that act as a dipole antenna. The qubit 110 is a substantially two-dimensional device that resides in a single plane. A dipole moment produced by the qubit, p_q , lies in the plane of the qubit 110. An electric field produced by the resonator, E_r , is directed perpendicular to the reflectors 131 and 132 (two illustrative field lines are shown). The qubit and resonator can be coupled to one another since the electric field of the resonator and the dipole moment of the qubit are aligned.

[0045] In the illustrative device of FIG. 1, both the dipole moment of the qubit and the electric field of the resonator lie in the plane defined by the planar qubit 110. However, the resonator also produces electric fields above and/or below the plane of the qubit. These fields can be detrimental to the performance of the device because they can contribute to radiation loss and/or cross-talk between different elements of the device. Accordingly, while it is necessary that the electric field be present in the plane of the qubit and aligned with the dipole moment of the qubit, the design of FIG. 1 leads to undesired effects within the qubit.

[0046] Thus, while superconducting qubits can be fabricated using conventional techniques, they also exhibit relatively shorter coherence times. Alternatively, three-dimensional devices such as device 100 shown in FIG. 1 offer relatively longer coherence times yet cannot be so easily fabricated and can also introduce detrimental effects during operation due to unwanted interactions between the qubit and electric field of the resonator.

[0047] The inventors have recognized and appreciated that qubits may be produced that can be fabricated using conventional techniques yet also exhibit relatively longer coherence times by forming planar multilayer circuits in which a qubit located within the plane of a wall of a resonator cavity is configured to produce a dipole moment directed into the cavity. Accordingly, the qubit can be fabricated in a planar fashion with the resonator cavity, thus allowing the use of conventional fabrication techniques, whilst the

qubit can be coupled to the resonator since its dipole moment is aligned with the electric field of the resonator.

[0048] FIG. 2 illustrates a quantum device in which a planar qubit is coupled to a non-planar resonator, according to some embodiments. In the example of FIG. 2, a qubit 210 is fabricated within a reflector 232 of a resonator defined by reflectors 231 and 232. As shown, the qubit 210 is configured to produce a dipole moment that, at least in one region of the resonator, is directed perpendicular to the reflector 232 and parallel to the electric field E_r produced by the resonator. As such, the qubit 210 may be coupled to the resonator defined by reflectors 231 and 232 yet the device shown may be formed in layers using conventional fabrication techniques, such as lithography. Moreover, the electric field of the resonator shown in FIG. 2 does not provide undesirable interactions with the qubit as is the case in device 100 shown in FIG. 1 and discussed above.

[0049] In general, device 200 may include any number of qubits such as qubit 210, since multiple qubits may be fabricated along one reflector of the resonator with some separation between them. Additionally, or alternatively, device 200 may include qubits at multiple different positions along a vertical direction of FIG. 2, such as within reflector 231 and/or within another reflector or other surface positioned above reflector 231 (not shown).

[0050] While the illustrative resonator shown in FIG. 2 includes two surfaces, namely reflectors 231 and 232, in general a resonator may be used in device 200 that includes any number of surfaces, including in some cases surfaces that prescribe a completely bounded volume. Surfaces of a resonator may also include one or more materials, at least some of which may be materials that may be operated to be superconducting (e.g., aluminum lowered to a suitable temperature at which it becomes superconducting). In some cases, a surface of a resonator may include multiple different materials.

[0051] According to some embodiments, qubit 210 may include one or more Josephson elements, which are non-linear, non-dissipative elements. As used herein with respect to a Josephson element, “nonlinear” refers to a flux-charge relationship (e.g., the inductance) of the element being nonlinear; and “non-dissipative” refers to the

fact that the amount of power dissipated by the element is substantially negligible. Any suitable Josephson element may be used, including but not limited to, Josephson junctions, superconducting films, and nanowires. In the embodiments described below, Josephson junctions are used. But it should be understood that the techniques and embodiments described herein are not limited to using Josephson junctions.

[0052] Following below are more detailed descriptions of various concepts related to, and embodiments of, techniques for coupling a planar quantum system to a non-planar resonator. It should be appreciated that various aspects described herein may be implemented in any of numerous ways. Examples of specific implementations are provided herein for illustrative purposes only. In addition, the various aspects described in the embodiments below may be used alone or in any combination, and are not limited to the combinations explicitly described herein.

[0053] As discussed above, qubit 210 provides a dipole moment that is perpendicular to the plane of the qubit. Any suitable qubit implementation may be used that produces such an effect, although two broad classes of such qubits are discussed below. First, qubits based on patch antenna, which are discussed in relation to FIGs. 3A-3B, 4A-4B and 5; and second, qubits based on a whispering gallery mode resonator, which are discussed in relation to FIGs. 6A-6C, 7A-7B and 8.

[0054] FIG. 3A illustrates a top view of a “patch antenna” 300 that is used in some embodiments to create the aforementioned dipole perpendicular to the plane of the qubit. The patch antenna 300 is formed by removing an annular aperture 305 with an outer radius r_o from a conducting sheet 310, resulting in a circular patch 320 with a radius r_i (representing the inner radius of the annular aperture 305) surrounded by the remaining conducting sheet 310. FIG. 3B illustrates a cross-sectional view of the patch antenna 300, where the cross-section is taken through the center of the circular patch 320.

[0055] When a voltage is applied across the annular aperture 305 between the circular patch 320 and the conducting sheet 310, two opposing dipole moments p_q are generated, as represented by arrows 330 and 331 in FIG. 3B. The dipole moments p_q are not directed within the plane of the patch antenna, but are instead directed perpendicular

to the plane of the patch antenna. The dipole moments are not illustrated in FIG. 3A, but point into and out of the drawing.

[0056] While a circular patch 320 is illustrated in FIGs. 3A-B, embodiments of a patch antenna are not necessarily so limited, as any suitable shape may be used to form a patch antenna. For instance, the patch 320 may instead be triangular, rectangular, polygonal, star-shaped or any other suitable shape. Moreover, both surfaces of the annular aperture 305 may be shaped to have any suitable contour. For example, the inner surface 306 of the annular aperture 305, determined by the shape of the patch 320, may be any contour. In the figure, inner surface 306 is illustrated as a circle, but the surface may be elliptical, rectangular, square and/or may include irregular or regular features such as periodic patterns (e.g., sinusoidal waves, triangular wave, square wave, etc.). Similarly, the outer surface 307 of the annular aperture 305 may be any suitable contour. Additionally, embodiments are not limited to the shape of inner surface 306 being the same shape as the outer surface 307. For example, the inner surface 306 may be circular (forming circular patch 320) while the outer surface 307 may be rectangular (forming a rectangular aperture in the conducting sheet 310). In general, any number of patches may be included within a patch antenna, being connected to one another and/or being connected to the conducting sheet (e.g., via one or more Josephson junctions).

[0057] Moreover, the patch 320 may be located anywhere within the aperture 305 as embodiments are not limited to the patch/aperture structure being circularly symmetric, nor indeed are embodiments limited to exhibiting any particular symmetry, such as 4-fold or 8-fold symmetry (though some embodiments may exhibit such a symmetry). FIGs. 3A-B illustrate a patch 320 that is circularly symmetric in that the circular patch 320 is in the center of the circular aperture 305. In some alternate embodiments, the circular patch 320 may be nearer to a first edge of the circular aperture 305 than a second edge of the aperture 305, thus producing a patch antenna that is not circularly symmetric.

[0058] The inventors have recognized and appreciated that by selecting the shape of the patch 320 and the aperture 305, as well as the location of the patch 320 within the aperture 305 the ratio of magnetic to electric coupling between the qubit and resonator can be tuned. By tuning this ratio, the resonance of the qubit may be tuned

independently from the resonance of the resonator such that it is separated from the resonance of the resonator (e.g., to produce a desired dispersive coupling between the qubit and resonator).

[0059] Also, while the circular patch was described above as being formed by removing an annular aperture 305 from a thin conducting sheet 310, the patch antenna 300 may also be formed by depositing a conductive material on a substrate to form the circular patch 320 and the conducting sheet 310 resulting in the formation of the annular aperture 305.

[0060] In some embodiments, one or more Josephson junctions may be added to the patch antenna structure described above to form a superconducting qubit. The Josephson junction may be disposed, for example, between the circular patch 320 and the conductive sheet 310 such that the two portions of the patch antenna are coupled together through the Josephson junction. A Josephson junction may be formed, for example, on a superconducting wire that forms a “bridge” between the circular patch 320 and the conductive sheet 310.

[0061] A Josephson junction may be formed, for example, by placing a thin non-superconducting tunnel layer between two superconducting layers. In some embodiments, such a non-superconducting layer may be a non-conducting material. For example, any suitable oxide, such as aluminum oxide may be used. In some embodiments, the patch antenna is formed from a superconducting material. By way of example and not limitation, the patch antenna may be formed from aluminum, niobium, indium, rhenium, tantalum, titanium nitride, niobium nitride, or combinations thereof.

[0062] While embodiments described herein illustrate only a single Josephson junction, some embodiments may include a plurality of Josephson junctions, which may be arranged in parallel or in series with one another. For example, two Josephson junctions in series may be formed on the superconducting wire connecting the circular patch 320 to the conductive sheet 310. Two Josephson junctions in parallel may be formed by using multiple “bridges” to connect the circular patch 320 to the conductive sheet 310, each bridge comprising one or more Josephson junctions.

[0063] As discussed above, a qubit such as qubit 210 shown in FIG. 2 may be embedded in a metal layer that forms a portion of a non-planar superconducting resonator. By way of example and not limitation, a three-dimensional cavity resonator or a transmission line resonator, such as a ring resonator, may be used. FIGs. 4A-4B illustrate an example of using a patch antenna, such as that described in relation to FIGs. 3A-3B that includes a Josephson junction as described above, within a three-dimensional cavity resonator.

[0064] FIG. 4A illustrates a cross-section of a quantum device 400 comprising a three-dimensional cavity. The cavity is that portion of the device that is not filled with any material (shown as white in the interior of the device in the figure). In some embodiments, the device may be placed in a vacuum during operation such that there is substantially no air in the cavity. The cavity is defined by a plurality of superconducting portions that act as walls for the cavity, including superconducting portions 412, 451, 452 and 453. In some embodiments, an interior surface of superconducting portions 451 and 452 may be substantially parallel to one another, while an interior surface of superconducting portion 452 may be substantially parallel to an interior surface of superconducting portion 412.

[0065] In some embodiments, as discussed in connection with FIGs. 3A-B, an annular shape may be formed in superconducting portion 412 to form a circular patch 414. In the example of FIGs. 4A-4B, the circular patch is connected to the superconducting portion 412 via a Josephson junction 415. FIG. 4B illustrates a perspective view of the superconducting portion 412 and the patch 414. Elements of the quantum device shown in FIG. 4A other than elements 412, 414 and 415 are not illustrated in FIG. 4B for the sake of clarity.

[0066] In the example of FIGs. 4A-4B, the combination of superconducting portions 412 and 414, and Josephson junction 415, form a logical qubit. As such, this combination of elements is a suitable example of qubit 210 shown in FIG. 2.

[0067] As an illustrative way to form device 400, in some embodiments, superconducting portions 451, 452 and 453 may be formed on a substrate 450. The substrate may be formed from, by way of example and not limitation, silicon, sapphire

and/or some other dielectric. In some embodiments, the superconducting portions 412, 414 and the Josephson junction 415 may be formed on a substrate 410, which may be formed from silicon, sapphire and/or some other dielectric. After each of the two substrates 410 and 450 have the respective superconducting portions and any other devices formed upon them, the two substrates may be affixed together to form the cavity illustrated in FIG. 4A. The two substrates may be affixed together in any suitable way. For example, two substrates that have been covered, at least partially, with a metal material may be bonded together using cold welding, thermocompression bonding, thermosonic bonding, eutectic bonding and/or solder reflow.

[0068] In some embodiments, the superconducting portion 412 may be formed from a single type of superconducting material. However, as illustrated in FIG. 4A, in some embodiments a first portion of the superconducting portion 412 is formed from a first superconducting material, such as aluminum (shown in shaded lines in FIGs. 4A-4B), and a second portion of the superconducting portion 412 is formed from a second superconducting material, such as indium (shown as solid black in FIGs. 4A-4B). Superconducting portions 451-453 may also be formed from the second superconducting material or a different material. According to some embodiments, superconducting portions 412 and 414 may be formed from aluminum, indium, tin, silicon carbide, or combinations thereof. As used herein, a “superconducting material” is a material that, at least under some conditions, exhibits a type of superconductivity. For instance, aluminum may be considered a “superconducting material” since it exhibits superconductivity when cooled below the transition temperature of 1.2K.

[0069] As discussed above, the Josephson junction 415 may act as a qubit that is coupled to the cavity of device 400 due to its dipole moment p_q coupling to an electric field of the cavity E_r . While FIG. 3B illustrated two dipole moments pointing in opposing directions, only one of those two dipole moments will couple to the field supported by the cavity, since the other is directed into substrate 410. In some embodiments, a material in which the Josephson junction 415 is embedded is a material that serves as a boundary of two different cavities (e.g., via two different surfaces of the material). In this way, the Josephson junction 415 may be coupled to two cavities simultaneously due to a dipole moment above the Josephson junction coupling to an

electric field of a first cavity and a dipole moment below the Josephson junction being coupled to an electric field of a second cavity.

[0070] FIG. 5 illustrates one embodiment in which a Josephson junction is coupled to two cavities. The same reference numerals are used in FIG. 5 as were used in FIGS. 4A-4B to indicate equivalent features. In the example of FIG. 5, the logical qubit formed from elements 412, 414 and 415 produces a dipole moment that couples to an electric field E_{r1} of a first cavity (lower as pictured) and also to an electric field E_{r2} of a second cavity (upper as pictured).

[0071] In the example of FIG. 5, the second cavity is bounded by material forming a box 510 that surrounds the substrate 410. According to some embodiments, the box 510 may comprise a metal, such as copper. According to some embodiments, walls of the second cavity may be formed from superconducting material 520 coated onto the inner surface box 510. In some embodiments, input coupler 512 and output coupler 514 are formed in the metallic box 510 and the superconducting material 520 to allow microwave radiation to be coupled into and out from the second cavity.

[0072] In some embodiments, the two cavities may have different Q factors. The first cavity may, for example, have a higher Q factor than the second cavity. As such, the coupling strength between the first (lower) cavity and the logical qubit may be less than the coupling strength between the logical qubit and the second (upper) cavity. Further, the coupling between the second cavity and a measuring device (not shown in the figure) may be greater than both the coupling strength between the first cavity and the logical qubit, and the coupling strength between the logical qubit and the second cavity. In some embodiments, the first cavity may be used as a readout cavity and the second cavity may be used as a storage cavity; the relative sizes of coupling strengths and/or Q factors referred to above may facilitate such an arrangement.

[0073] Quantum devices with components of any suitable size may be used. In one embodiment, the circular patch 414 has a radius $r_i = 0.1 - 0.2 \text{ mm}$ and the annular shape cut out from the superconducting portion has a radius $r_o = 0.7 - 0.8 \text{ mm}$. The substrate on which the Josephson junction is formed may have a thickness between 0.2 mm and 0.4 mm. The storage cavities may have different dimensions from one another. For

example, each cavity may have a volume below 200 cm^3 , or between 50 cm^3 and 150 cm^3 (e.g., the first cavity may measure approximately $22 \times 24 \times 0.3 \text{ mm}$, while the second cavity may measure $28 \times 30 \times 3 \text{ mm}$). The above measurements are provided by way of example, as embodiments are not limited to any particular sizes or shapes.

[0074] As discussed above, qubit 210 shown in FIG. 2 provides a dipole moment that is perpendicular to the plane of the qubit, and may for example be configured as a whispering gallery mode resonator (WGMR) or other planar multilayer device (sometimes referred to as a “2.5-dimensional device”).

[0075] A WGMR is formed, conceptually, by considering a parallel plate transmission line 600 with periodic boundary conditions, as illustrated in FIG. 6A. The parallel plate transmission line 600 comprises a top plate 601 and a bottom plate 602 that formed from superconducting materials, such as aluminum or indium. The top plate 601 is parallel to the bottom plate 602. FIG. 6A illustrates the electric and magnetic field modes of the WGMR as arrows that are perpendicular and parallel, respectively, to the planes defined by the top plate 601 and the bottom plate 602.

[0076] Physically, a WGMR 610 with periodic boundary condition may be formed by forming a parallel plate transmission line as a ring-like structure, as illustrated in FIG. 6B. The WGMR 610 comprises a top plate 611 and a bottom plate 612 that are parallel to one another, just as in the parallel plate transmission line 600, although in the example of FIG. 6B the transmission line forms a loop.

[0077] While a resonator may utilize a circularly symmetric pair of metal rings, in the WGMR resonator example of FIG. 6B, such circular symmetry of the ring-like structure is broken by forming the ring using two offset circles - that is, the holes in each metal ring are not centered with respect to the outer boundary of the metal ring. Thus, a symmetry plane, represented by dashed line 613, which lies parallel to the plane of each of the two metal rings and passes through the center of each of the two circles, is created.

[0078] By breaking the circular symmetry of the ring-like structure, two non-degenerate standing modes are created. The first non-degenerate standing mode is parallel to the symmetry axis and the second non-degenerate standing mode is perpendicular to the symmetry axis. The modes may further be separated into common

and differential modes, where the common modes (C) have mirror charges on the upper plate 611 and the lower plate 612 and differential modes (D) have opposite charges on the upper plate 611 and lower plate 612. In some embodiments, the two differential modes of the WGMR may be considered two separate cavities for coupling to a qubit (which may be included in the WGMR resonator as described below). By way of example, and not limitation, the parallel D mode may be used as a readout cavity and the perpendicular D mode may be used as a storage cavity.

[0079] FIG. 6C illustrates the parallel differential (D) mode in a cross sectional view of the WGMR 610. In the example of FIG. 6C, spacers 650 and 651 and substrates 621 and 622 are included to mechanically support the resonator formed from plates 611 and 612. In addition, coupling pins 630-631 are disposed above the ring-like structure, and may for example be used to couple microwave radiation to the WGMR. In the example of FIG. 6C, the coupling pins are located along the symmetry line 613 above the thinnest and thickest portions of the ring-like structure, although in general the coupling pins may be located in any suitable location.

[0080] As an illustrative example of a fabrication process, the device illustrated in FIG. 6C may be fabricated by forming the top plate 611 on a first substrate 621 and the bottom plate 612 on a second substrate 620. The first substrate 621 and the second substrate 622 may comprise, by way of example and not limitation, silicon and/or sapphire. The first substrate 621 and the second substrate 622 are then placed parallel to one another and held separated by a set distance by spacers 650-651, which may also be made from silicon and/or sapphire. As a non-limiting example, the distance between the two substrates may be between 0.1 mm and 0.3 mm.

[0081] The first substrate 621 and the second substrate 622 may then be bonded together using any suitable technique, such as by using Poly(methyl methacrylate) (PMMA). The resulting resonator may then be placed in a sample holder 640, which may be formed from a metal, such as aluminum. Coupling pins 630-631 may be disposed above the ring-like structure for coupling microwave radiation to the WGMR. In some embodiments, the coupling pins are located along the symmetry line 613, above the thinnest and thickest portions of the ring-like structure.

[0082] As with the above-described three-dimensional cavity resonator, a qubit may be embedded in the plane of one of the superconducting walls that defines the cavity – in the case of the WGMR, either within the top plate 611 or the bottom plate 612. FIGs. 7A and 7B depict two illustrative locations for such a qubit, and FIG. 8 provides additional detail of the structure of the qubits shown in FIGs. 7A and 7B.

[0083] FIG. 7A illustrates an embodiment where a qubit 710 is located at the thinnest portion of the ring-like structure. FIG. 7B illustrates an embodiment where a qubit 720 is located at an angle θ away from the thinnest portion of the ring-like structure, where $\theta=0$ is defined as the thinnest portion of the ring-like structure. The frequency with which the WGMR resonates is independent of the position of the qubit is located. However, the magnitude of the coupling of the qubit to the resonator varies with the position of the qubit around the ring 612. Moreover, for a given position θ , the magnitude of the coupling of the qubit to the resonator can be adjusted by changing the dimensions of the aperture in the WGMR.

[0084] With the qubit at the thinnest part of the ring ($\theta=0$), the storage mode has maximum coupling despite the fact that the electric field at this location is zero. This coupling is mostly inductive coupling. Varying the location of the qubit changes the coupling from inductive to capacitive coupling. According to some embodiments, The Q factor of the resonators and/or the coupling of resonator radiation to each mode may be a function of the angular position of the pins 630 and 631 and/or the depth that the pins 630 and 631 protrude into the cavity.

[0085] According to some embodiments, for dispersive coupling between the qubit and a resonator mode of a WGMR that utilizes the ring 612 as shown in FIG. 7A or 7B, the strength of the cross-Kerr coupling (χ_{qr}) depends primarily on the detuning (difference in frequencies) between the resonator transition frequency and the qubit transition frequency. In embodiments in which a WGMR is operated in a storage (memory) mode and in a readout mode, the cross-Kerr coupling constant between the qubit and the readout cavity (χ_{qr}) and the cross-Kerr coupling constant between the qubit and the memory cavity (χ_{qm}) are dependent on the location of the Josephson Junction.

[0086] FIG. 8 illustrates a top view of an illustrative qubit that may be utilized within a WGMR, such as qubit 710 shown in FIG. 7A and/or as qubit 720 shown in FIG. 7B. In the example of FIG. 8, a qubit 830 is formed from a rectangular patch 810 embedded in the plane of a bottom plate (of which plate 612 shown in FIG. 6B is depicted as an example).

[0087] The rectangular patch 810 may comprise the same superconducting material as the plate 612, and/or may comprise a different superconducting material. The plate 612 may be connected to the rectangular patch 810 via a Josephson junction 820. The qubit 830 may be located at any suitable location in the WGMR, and there may be any number of such qubits located in a lower WGMR plate and/or in an upper WGMR plate.

[0088] The superconducting devices discussed above may be fabricated in any suitable way. In some embodiments, microelectronic fabrication techniques may be used to form three-dimensional cavities for use as resonators, as described above.

Alternatively, the cavities may be formed using substrates where troughs and channels are formed as desired using three-dimensional printing techniques and the superconducting layers may be formed using, for example, electroplating techniques. According to some embodiments, enclosures are created by forming a trough in a single substrate, as illustrated in FIG. 4A. Alternatively, or in addition, enclosures may be created by forming a first trough in a first substrate and a second trough in a second substrate and placing the two substrates together with the two troughs adjacent to one another. A qubit, as described above, may be formed in any one of the superconducting surfaces used to form the cavity. Methods for forming superconducting devices according to some embodiments are described below.

[0089] FIGs. 9A-9J illustrate a cross-sectional view of a plurality of acts of an illustrative method for constructing a superconducting device, according to some embodiments. A flowchart of the corresponding acts is shown as method 1100 in FIG. 11. An initial act 1102 in FIG. 11 in which a trough is formed in a first substrate is depicted by FIGs. 9A-9G. These steps are also shown in greater detail by the acts of method 1200 shown in FIG. 12.

[0090] FIG. 9A illustrates a first substrate 900 being provided. In some embodiments, the substrate may comprise a material with a crystalline structure, such as, but not limited to, silicon or germanium. The substrate 900 may be of any suitable thickness. In the illustrated embodiments, the substrate is approximately 500 μm thick.

[0091] The initial act 1120 of method 1100, is shown in further detail in FIG. 12. Accordingly, steps of the method 1200 will be followed for the steps depicted in FIGs. 9A-9G.

[0092] At act 1202, a mask material layer 902 is deposited on a first surface of the substrate 900 (see FIG. 9B). According to some embodiments, the mask material layer may comprise silicon nitride. At act 1204, a photoresist layer 904 is deposited on top of the mask material layer 902 (see FIG. 9C). The photoresist layer 904 is formed in a pattern based on the dimensions of the trough being formed in the substrate 900. Accordingly, the photoresist layer 904 is absent from the region above where the trough will be formed in the substrate 900 in the subsequent acts. By way of example and not limitation, the photoresist layer 904 may be formed such that an area of the silicon mask material layer 902 with dimensions 18 mm by 38 mm is left exposed.

[0093] At act 1206, the exposed portion of the mask material layer 902 is removed (see FIG. 9D). This may be achieved in any suitable way. In some embodiments, the mask material layer 902 is etched using an etchant that removes the mask material layer, but does not remove the photoresist layer 904. For example, reactive ion etching (RIE) may be used to etch the silicon nitride layer 902. The act of RIE may use, for example, CHF_3/O_2 as an etchant. The photoresist layer 904 is then removed at act 1208. The resulting structure is the substrate 900 partially covered with the silicon nitride layer 902 which will act as a mask for defining dimensions of the trough (see FIG. 9E).

[0094] At act 1210, the exposed portion of the substrate 900 is etched to form a trough 906. In some embodiments, the substrate 900 may be etched such that opposing surfaces of the resulting trough 906 are parallel to one another. In the embodiment shown in FIG. 9F, the trough is etched using an anisotropic wet etch using 30% KOH at 85°C. The details of the anisotropic etch is shown in more detail in FIG. 10.

[0095] FIG. 10 illustrates the trough 906 resulting from an anisotropic wet etch. Because of the crystalline structure of the silicon substrate 900, the (100) plane 1012 and the (111) 1014 plane for a 54.7° angle as a result of the etching act. In some embodiments, the anisotropic wet etch results in surfaces 1012 and 1014 that are atomically smooth. Thus, when covered in a superconducting layer the surface of the resulting enclosure will be substantially free from defects. If the enclosure is configured for use as a three-dimensional cavity resonator, the smooth surfaces result in a high Q factor cavity.

[0096] At act 1212, the mask material layer 902 is removed resulting in the substrate 900 including the trough 906 (see FIG. 9G). While FIG. 12 illustrated one embodiment of a method for creating a trough in a substrate, any suitable method may be used. For example, laser machining or three-dimensional printing may be used to form a substrate with a trough.

[0097] Returning to FIG. 11, after the trough 906 is formed in a substrate at act 1102 the method 1100 continues at act 1104, where at least a portion of the first substrate 900 is covered with a superconducting material. In some embodiments, all the surfaces of the trough in the substrate may be covered. In other embodiments, only portions of the surfaces may be covered. For example, the patch and aperture structure described above may be formed in at least one of the surfaces formed from the superconducting material. Also, other apertures may be formed for, e.g., coupling electromagnetic radiation into the cavity. In some embodiments, portions of the substrate outside of the region associated with the trough may also be covered with a superconducting layer.

[0098] The superconducting layer may be formed in any suitable way. For example, FIGs. 9H-I illustrate one particular method for forming a superconducting layer 910 that covers at least a portion of the substrate. FIG. 9H illustrates a thin seed layer 908 deposited over the surface of the substrate 900. This may be done in any suitable way. In some embodiments, copper is deposited via evaporation techniques to form the seed layer 908. Any suitable thickness of seed layer may be used. For example, the seed layer 908 may be approximately 200 nm thick. While copper is used as an example material for the seed layer 908, any suitable material may be used.

[0099] FIG. 9I illustrates a superconducting layer 910 formed on the seed layer 908. This may be done in any suitable way. For example, a superconducting material 910 may be electroplated onto the seed layer 908. The superconducting layer 910 may be formed with any suitable thickness. For example, the superconducting layer 910 may be approximately 9 μm thick. Any suitable superconducting material may be used. For example, the superconducting layer may comprise aluminum, niobium, indium, rhenium, tantalum, titanium nitride, niobium nitride or combinations thereof.

[00100] At act 1106, a second trough is formed in a second substrate 950. The act of forming the second trough may be achieved using the same techniques described in connection with act 1102, FIG. 9 and FIG. 12. However, the formation of the second trough is optional. An enclosure may be formed from a single trough in a first substrate without forming a second trough in a second substrate.

[00101] At act 1108, at least a portion of the second substrate 950 is covered with a superconducting material 960. This act may be achieved using the techniques described in connection with act 1104. In embodiments where a second trough is formed in the second substrate 950, at least a portion of every surface of the trough may be covered with a superconducting layer 960. In some embodiments, a portion of the second substrate outside of the trough region may be at least partially covered with a superconducting layer.

[00102] At act 1110, at least one superconducting qubit is formed in the plane of the superconducting layer of at least one of the first substrate and the second substrate. This act may be performed at the time the superconducting layers are formed on the substrate. However, in other embodiments, the superconducting qubit may be formed prior to or after covering the trough with superconducting material. In some embodiments, act 1110 may be omitted as superconducting devices may be formed with an enclosure and without a superconducting qubit.

[00103] At act 1112, the first substrate and the second substrate are bonded together to form an enclosure (see FIG. 9J). In embodiments where the first trough was formed in the first substrate and a second trough was formed in the second substrate, the two troughs are positioned adjacent to one another such that the enclosure is formed from

both troughs together. In some embodiments where at least one superconducting qubit is to be enclosed by an enclosure, the support layer is suspended across the first trough prior to bonding the two substrates together. Accordingly, the at least one qubit in and/or on the support layer is disposed within the enclosure.

[00104] Having thus described several aspects of at least one embodiment of this invention, it is to be appreciated that various alterations, modifications, and improvements will readily occur to those skilled in the art.

[00105] Such alterations, modifications, and improvements are intended to be part of this disclosure, and are intended to be within the spirit and scope of the invention. Further, though advantages of the present invention are indicated, it should be appreciated that not every embodiment of the technology described herein will include every described advantage. Some embodiments may not implement any features described as advantageous herein and in some instances one or more of the described features may be implemented to achieve further embodiments. Accordingly, the foregoing description and drawings are by way of example only.

[00106] Various aspects of the present invention may be used alone, in combination, or in a variety of arrangements not specifically discussed in the embodiments described in the foregoing and is therefore not limited in its application to the details and arrangement of components set forth in the foregoing description or illustrated in the drawings. For example, aspects described in one embodiment may be combined in any manner with aspects described in other embodiments.

[00107] Also, the invention may be embodied as a method, of which an example has been provided. The acts performed as part of the method may be ordered in any suitable way. Accordingly, embodiments may be constructed in which acts are performed in an order different than illustrated, which may include performing some acts simultaneously, even though shown as sequential acts in illustrative embodiments.

[00108] Use of ordinal terms such as “first,” “second,” “third,” etc., in the claims to modify a claim element does not by itself connote any priority, precedence, or order of one claim element over another or the temporal order in which acts of a method are performed, but are used merely as labels to distinguish one claim element having a

certain name from another element having a same name (but for use of the ordinal term) to distinguish the claim elements.

[00109] Also, the phraseology and terminology used herein is for the purpose of description and should not be regarded as limiting. The use of “including,” “comprising,” or “having,” “containing,” “involving,” and variations thereof herein, is meant to encompass the items listed thereafter and equivalents thereof as well as additional items.

[00110] What is claimed is:

Claims

1. A quantum circuit, comprising:
a resonator having a plurality of superconducting surfaces and configured to support at least one electromagnetic oscillation mode within a three-dimensional region defined by walls on which are disposed the plurality of superconducting surfaces; and
a physical qubit disposed in an opening in one of the walls.
2. The system of claim 1, wherein the physical qubit comprises at least one planar component that includes at least one Josephson element.
3. The system of claim 2, wherein the at least one planar component includes a superconducting patch antenna.
4. The system of claim 3, wherein the superconducting patch antenna comprises a patch with a circular shape.
5. The system of claim 3, wherein the superconducting patch antenna comprises a patch with a rectangular shape.
6. The system of claim 3, wherein a superconducting patch of the superconducting patch antenna is connected to the first superconducting surface via at least one Josephson element.
7. The system of claim 1, wherein the resonator is a three dimensional cavity resonator.
8. The system of claim 1, wherein the resonator is a whispering gallery mode resonator.
9. The system of claim 8, wherein the whispering gallery mode resonator includes the first superconducting surface and a second superconducting surface parallel to the first superconducting surface, and wherein the first superconducting surface is separated from the second superconducting surface by a first distance.

10. The system of claim 9, wherein the whispering gallery mode resonator supports at least two electromagnetic oscillation modes.
11. The system of claim 10, wherein the at least two electromagnetic oscillation modes are differential modes.
12. The system of claim 10, wherein a first electromagnetic oscillation mode of the at least two electromagnetic oscillation modes is a parallel mode.
13. The system of claim 12, wherein a second electromagnetic oscillation mode of the at least two electromagnetic oscillation modes is a perpendicular mode.
14. The system of claim 9, wherein the first superconducting surface is a first ring-like structure and the second superconducting surface is a second ring-like structure.
15. The system of claim 14, wherein the first ring-like structure is circularly asymmetric such that a first width of the first ring-like structure in a first plane at a first location is less than a second width of the first ring-like structure in the first plane at a second location, different from the first location.
16. The system of claim 1, wherein the quantum mechanical system comprises a plurality of resonators.
17. The system of claim 16, wherein a first resonator of the plurality of resonators is a readout cavity.
18. The system of claim 17, wherein a second resonator of the plurality of resonators is a storage cavity.
19. The system of claim 1, wherein:

the plurality of superconducting surfaces include a first superconducting surface that defines a first plane;

the opening is in a first wall on which the first superconducting surface is disposed;
and

the physical qubit comprises at least one planar component that is within the first plane.